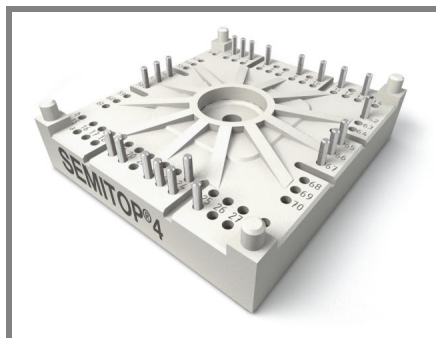


SK100GD12T4T



SEMITOP® 4

IGBT Module

SK100GD12T4T

Target Data

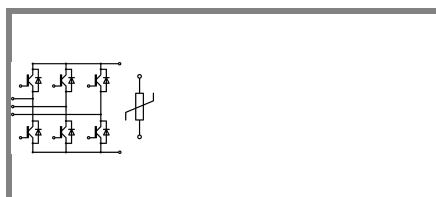
Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench4 IGBT technology
- CAL4 technology FWD
- Integrated NTC temperature sensor

Typical Applications*

Remarks

- $V_{CE,sat}$, V_F = chip level value

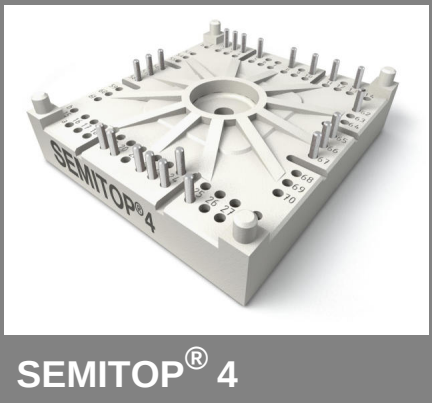


GD-T

Absolute Maximum Ratings				$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions			Values	Units
IGBT					
V_{CES}	$T_j = 25\text{ °C}$			1200	V
I_C	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$		126	A
		$T_s = 70\text{ °C}$		100	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$			300	A
V_{GES}				± 20	V
t_{psc}	$V_{CC} = 800\text{ V}$; $V_{GE} \leq 15\text{ V}$; $T_j = 150\text{ °C}$ $V_{CES} < 1200\text{ V}$			10	μs
Inverse Diode					
I_F	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$		102	A
		$T_s = 70\text{ °C}$		81	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$			300	A
I_{FSM}	$t_p = 10\text{ ms}$; half sine wave $T_j = 150\text{ °C}$			548	A
Module					
$I_{t(RMS)}$					A
T_{vj}				-40 ... +175	$^{\circ}\text{C}$
T_{stg}				-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.			2500	V

Characteristics			T _s = 25 °C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 3,4 mA		5	5,8	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES}	T _j = 25 °C T _j = 125 °C	0,02			mA mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V	T _j = 25 °C T _j = 125 °C	1200			nA nA
V _{CE0}		T _j = 25 °C T _j = 150 °C		1,1 1	1,3 1,2	V V
r _{CE}	V _{GE} = 15 V	T _j = 25°C T _j = 150°C		7,5 12,5		mΩ mΩ
V _{CE(sat)}	I _{Cnom} = 100 A, V _{GE} = 15 V	T _j = 25°C _{chiplev.} T _j = 150°C _{chiplev.}		1,85 2,25	2,05 2,45	V V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz		5,54			nF
C _{oes}			0,41			nF
C _{res}			0,32			nF
Q _G	V _{GE} = -7V..+15V		750			nC
R _{Gint}	T _j = 25 °C		2			Ω
t _{d(on)}	R _{Gon} = 16 Ω di/dt = 1800 A/μs	V _{CC} = 600V I _C = 100A T _j = 150 °C V _{GE} = ±15 V	63			ns
t _r			65			ns
E _{on}			16,6			mJ
t _{d(off)}	R _{Goff} = 16 Ω	T _j = 150 °C V _{GE} = ±15 V	521			ns
t _f	di/dt = 1800 A/μs		80			ns
E _{off}			10			mJ
R _{th(j-s)}	per IGBT		0,43			K/W

SK100GD12T4T



IGBT Module

SK100GD12T4T

Target Data

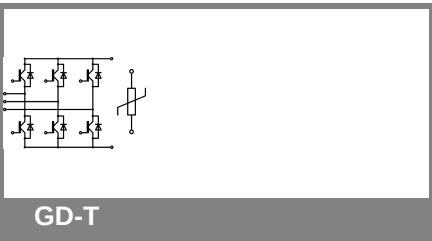
Features

- One screw mounting module
- Fully compatible with SEMISTOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench4 IGBT technology
- CAL4 technology FWD
- Integrated NTC temperature sensor

Typical Applications*

Remarks

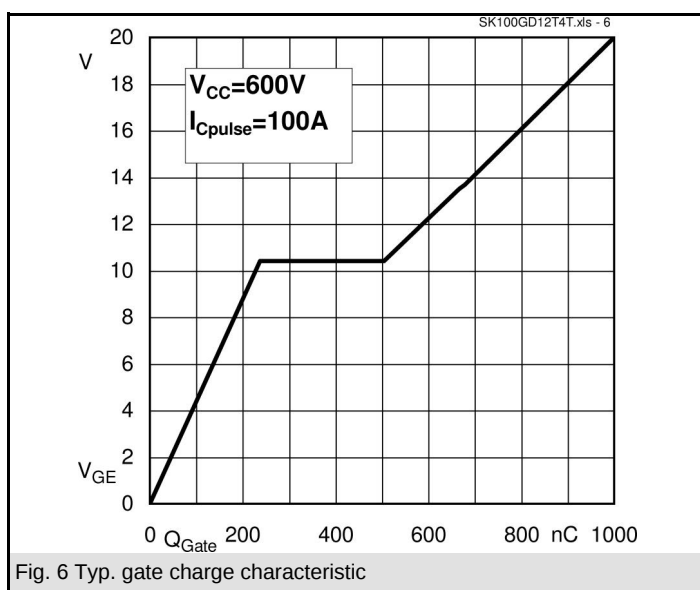
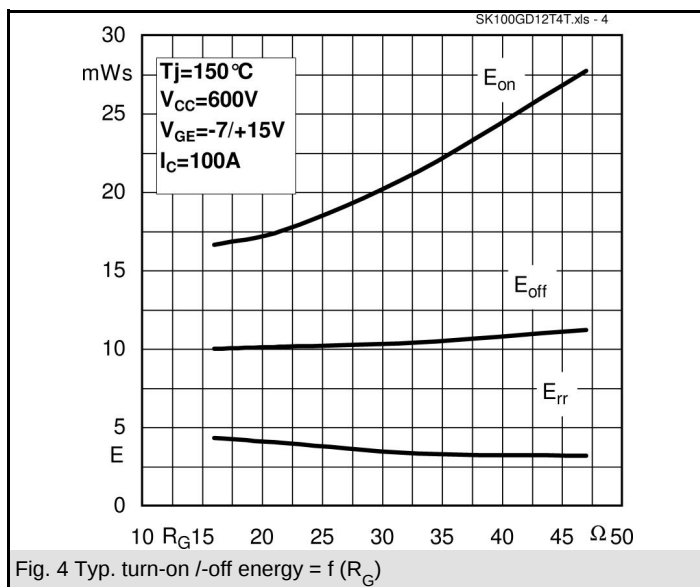
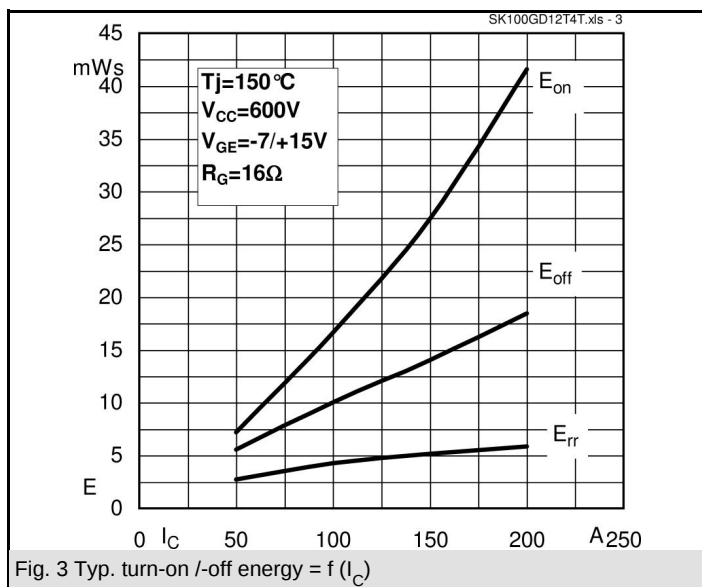
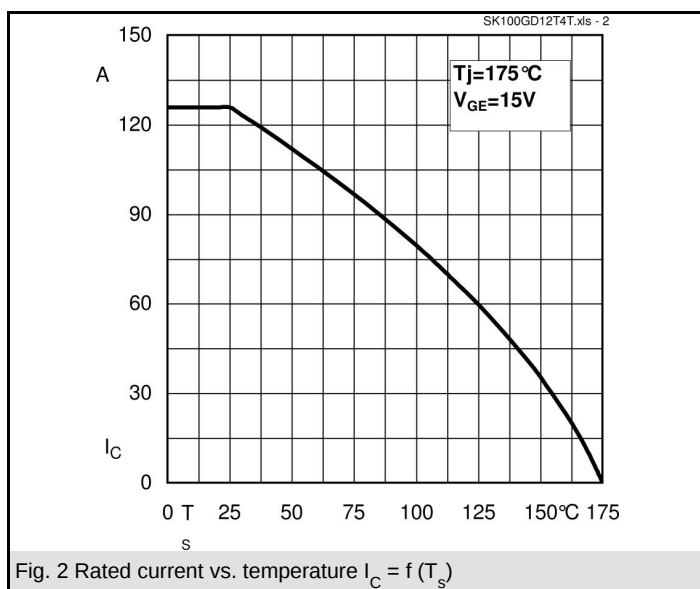
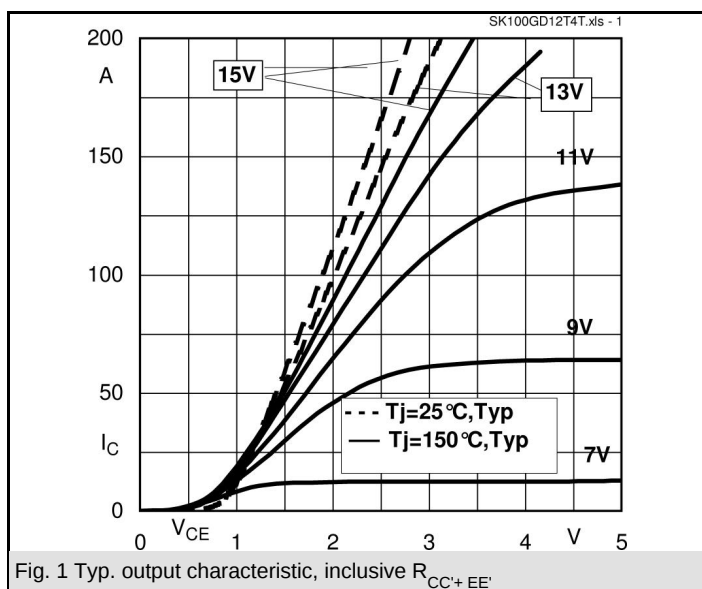
- $V_{CE,sat}$, V_F = chip level value

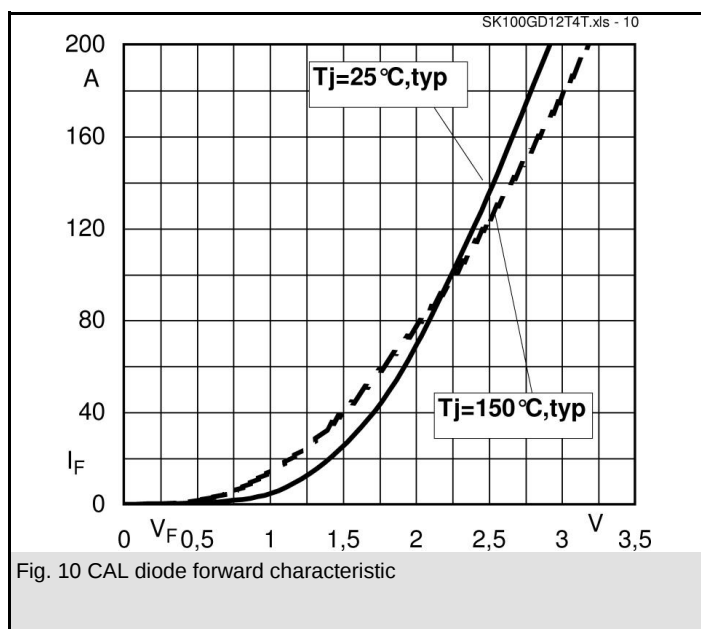
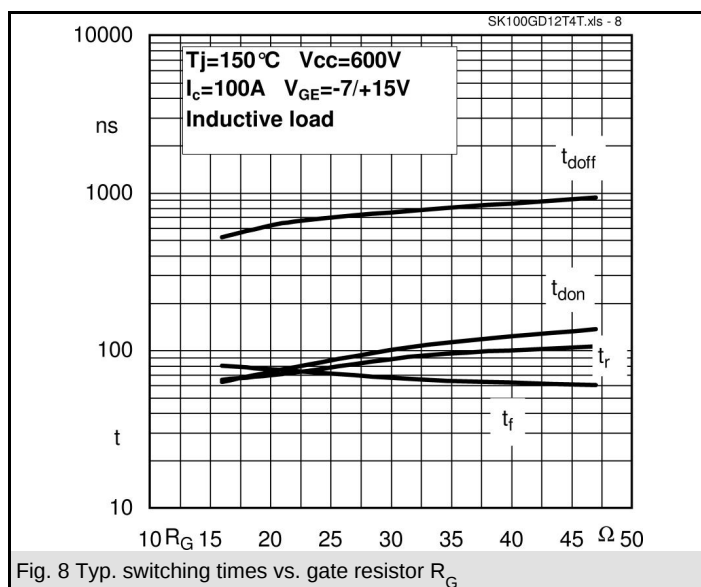
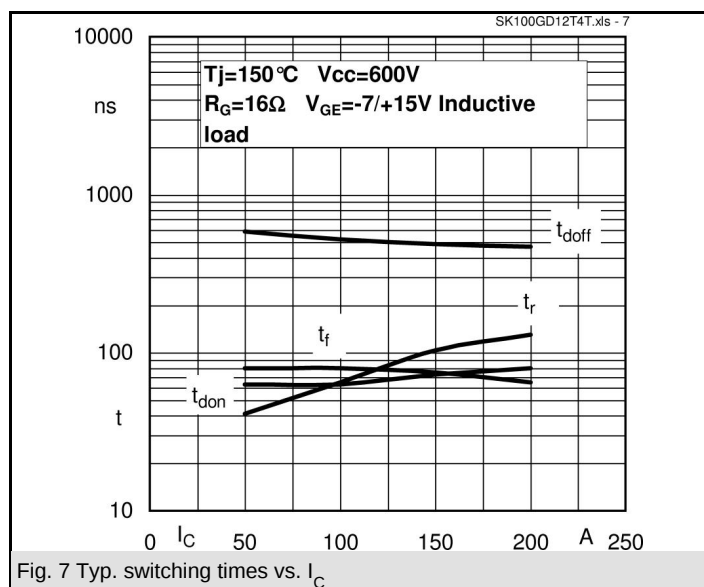


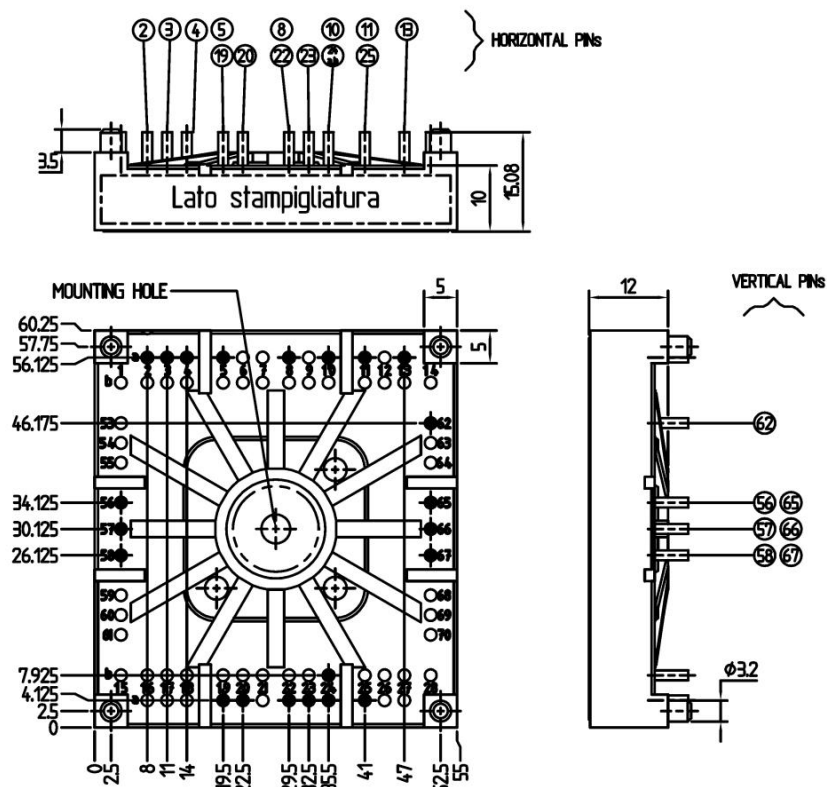
Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
V _F = V _{EC}	I _{Fnom} = 100 A; V _{GE} = 0 V	T _j = 25 °C _{chiplev.}	2,25	2,55	V
		T _j = 150 °C _{chiplev.}	2,2	2,5	V
V _{F0}		T _j = 25 °C	1,3	1,5	V
		T _j = 150 °C	0,9	1,1	V
r _F		T _j = 25 °C	9,5	10,5	mΩ
		T _j = 150 °C	13	14	mΩ
I _{RRM}	I _F = 100 A	T _j = 150 °C	52		A
Q _{rr}	di/dt = 1800 A/μs		14		μC
E _{rr}	V _{CC} = 600V		5,2		mJ
R _{th(j-s)D}	per diode		0,62		K/W
M _s	to heat sink	2,5		2,75	Nm
w			60		g
Temperature sensor					
R ₁₀₀	T _s =100°C (R ₂₅ =5kΩ)		493±5%		Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

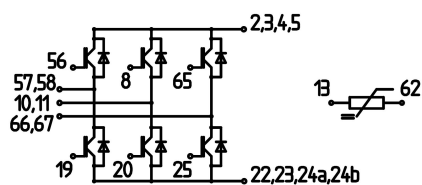
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.







Case T74 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)



Case T 74

GD-T